

isc N-Channel MOSFET Transistor

SPI11N65C3

• FEATURES

- Static drain-source on-resistance:
 R_{DS}(on) ≤0.38Ω
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

- · Ultra low gate charge
- High peak current capability

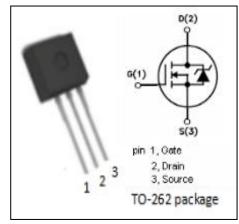


• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	650	V	
V _G s	Gate-Source Voltage	ate-Source Voltage ± 20		
I _D	Drain Current-Continuous	11	А	
Ірм	Drain Current-Single Pulsed	33	А	
P _D	Total Dissipation @T _C =25°C	125	W	
Tj	Max. Operating Junction Temperature	150	${\mathbb C}$	
T _{stg}	Storage Temperature	-55~150	${\mathbb C}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1	°C/W	



	13 D1 H2			[4]
		n	ım	
	DIM	MIN	MAX	
	A	4.37	4.77	
	A1	1.22	1.42	
	A2	2.47	2.87	
	Ъ	0.70	0.97	
	Ъ2	1.17	1.42	
	С	0.28	0.53	
	D	23.20	24.02	1
	D1	8.38	8.90	1
	D2	6.00	-8	1
	E	9.90	10.39	1
	E4	7.30		1
	е	2.54BSC		1
	G	1.25	1.50	
	H2	10 00	1.31	
	L	13.34	14.10	1
	L1	3.30	4.06	l



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	650			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =0.5mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; ID=7A			0.38	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V; V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	I _F =Is; V _{GS} = 0V			1.2	V

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